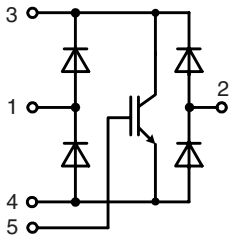
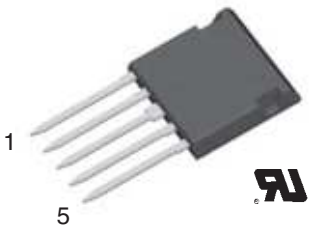
Bidirectional Switch with NPT³ IGBT and fast Diode Bridge

in ISOPLUS i4-PAC™

I_{C25} = 50 A
V_{CES} = 1200 V
$V_{CE(sat)\,typ.}$ = 2.0 V





IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	1200	V
V_{GES}		± 20	V
I_{C25}	T_C = 25°C	50	A
I_{C90}	T_C = 90°C	32	A
I_{CM}	V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C	50	A
V_{CEK}	RBSOA, Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = 900V; V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	200	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 30 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.0	2.6	V
	T_{VJ} = 125°C		2.3		V
$V_{GE(th)}$	I_C = 1 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.4	mA
	T_{VJ} = 125°C		0.4		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		85		ns
t_r	V_{CE} = 600 V; I_C = 30 A		50		ns
$t_{d(off)}$	V_{GE} = ±15 V; R_G = 39 Ω		440		ns
t_f			50		ns
E_{on}			4.6		mJ
E_{off}			2.2		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		2		nF
Q_{Gon}	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 35 A		150		nC
R_{thJC}				0.6	K/W
R_{thJS}			1.2		K/W

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Features

- NPT³ IGBT
  - low saturation voltage
  - positive temperature coefficient for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diodes
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
- ISOPLUS i4-PAC™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - enlarged creepage towards heatsink
  - application friendly pinout
  - low inductive current path
  - high reliability
  - industry standard outline
  - UL registered, E 72873

Applications

switches to control bidirectional current flow by a single control signal:

- matrix converters
- spare matrix converters
- AC controllers

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Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	48	A
I_{F90}	T_C = 90°C	25	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 30 A; T_{VJ} = 25°C		2.4	2.8	V
	T_{VJ} = 125°C		1.8		V
I_{RM}			27		A
t_{rr}			150		ns
R_{thJC}	(per diode)			1.3	K/W
R_{thJS}			1.6		K/W

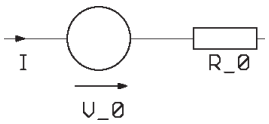
Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq$ 1 mA; 50/60 Hz	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values min.	typ.	max.	
C_p	coupling capacity between shorted pins and mounting tab in the case		40		pF
d_S,d_A	pin - pin	1.7			mm
d_S,d_A	pin - backside metal	5.5			mm
Weight			9		g

Equivalent Circuits for Simulation

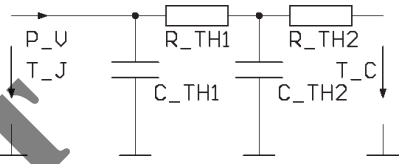
Conduction



IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V_0 = 0.95 V; R_0 = 45 mΩ

Diode (typ. at T_J = 125°C)
V_0 = 1.26V; R_0 = 15 mΩ

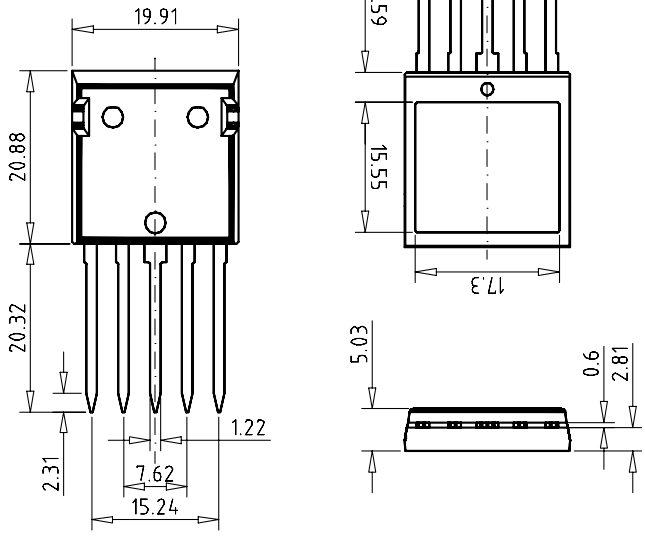
Thermal Response



IGBT
C_{th1} = 0.067 J/K; R_{th1} = 0.108 K/W
C_{th2} = 0.175 J/K; R_{th2} = 0.491 K/W

Diode
C_{th1} = 0.039 J/K; R_{th1} = 0.337 K/W
C_{th2} = 0.090 J/K; R_{th2} = 0.963 K/W

Dimensions in mm (1 mm = 0.0394")



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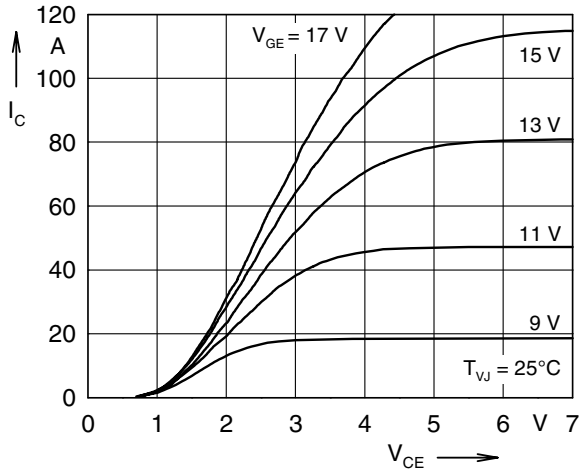


Fig. 1 Typ. output characteristics

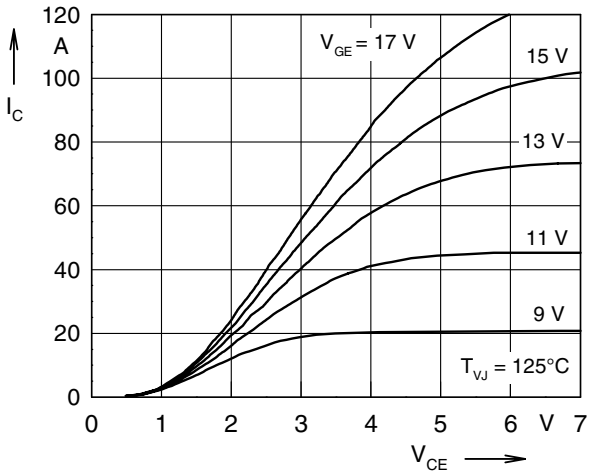


Fig. 2 Typ. output characteristics

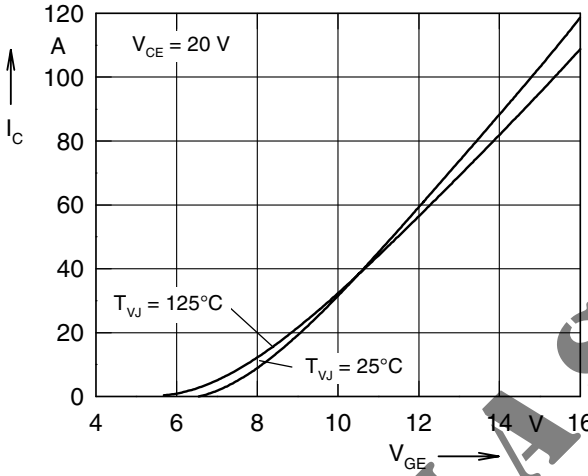


Fig. 3 Typ. transfer characteristics

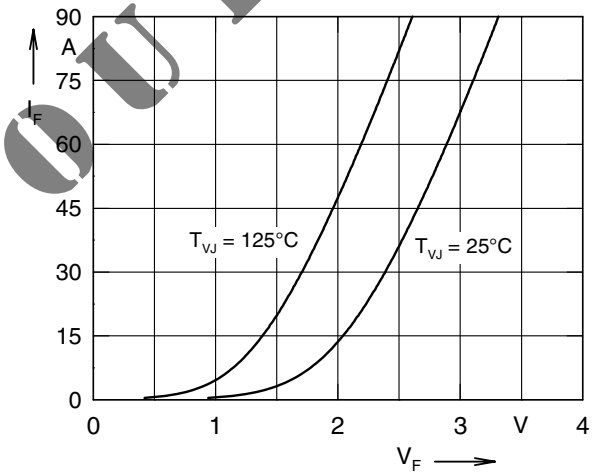


Fig. 4 Typ. forward characteristics of free wheeling diode

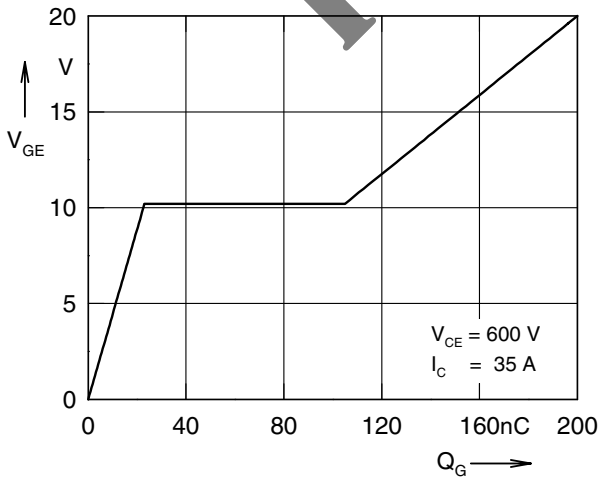


Fig. 5 Typ. turn on gate charge

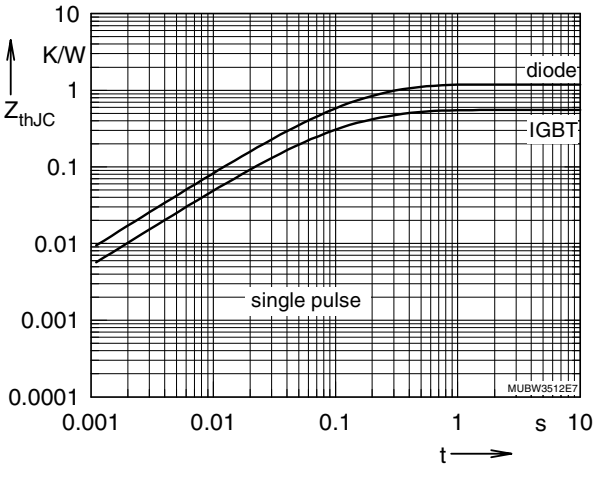


Fig. 6 Typ. transient thermal impedance

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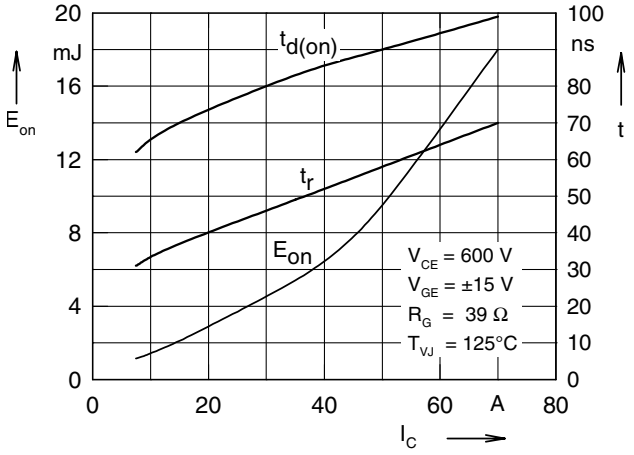


Fig. 7 Typ. turn on energy and switching times versus collector current

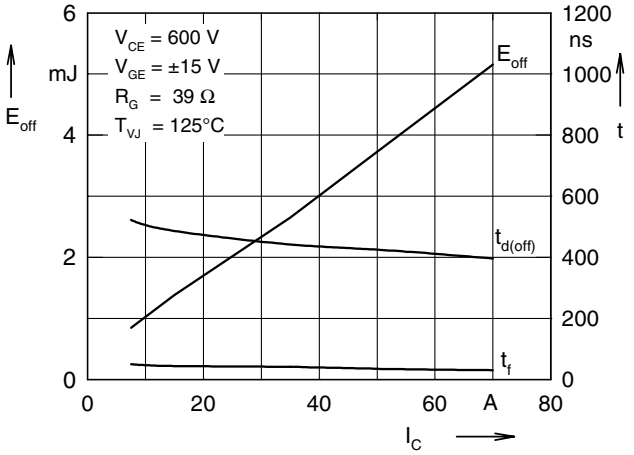


Fig. 8 Typ. turn off energy and switching times versus collector current

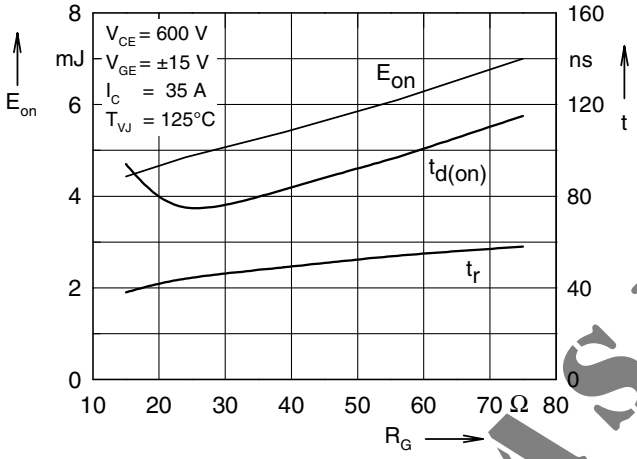


Fig. 9 Typ. turn on energy and switching times versus gate resistor

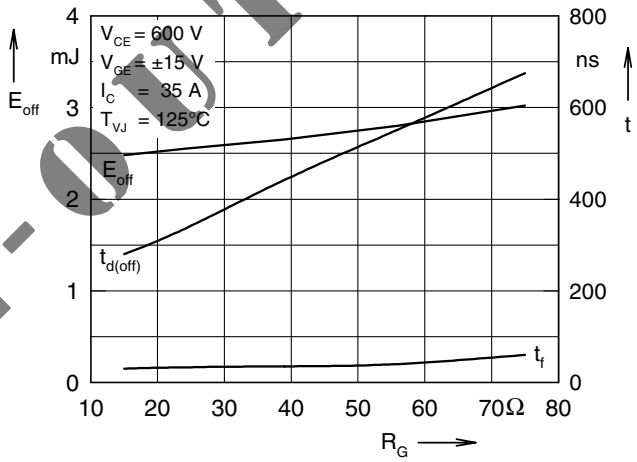


Fig.10 Typ. turn off energy and switching times versus gate resistor

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